

HEF40174B

Hex D-type flip-flop

Rev. 05 — 6 January 2010

Product data sheet

1. General description

The HEF40174B is a hex edge-triggered D-type flip-flop with six data inputs (D0 to D5), a clock input (CP), an overriding asynchronous master reset input (MR), and six buffered outputs (Q0 to Q5). Information on D0 to D5 is transferred to Q0 to Q5 on the LOW-to-HIGH transition of CP if MR is HIGH. When LOW, MR resets all flip-flops (Q0 to Q5 = LOW) independent of CP and D0 to D5.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input. It is also suitable for use over the full industrial (−40 °C to +85 °C) temperature range.

2. Features

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the full industrial temperature range −40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. Applications

- Industrial
- Shift registers
- Buffer/storage register
- Pattern generator

4. Ordering information

Table 1. Ordering information

All types operate from −40 °C to +85 °C.

Type number	Package		
	Name	Description	Version
HEF40174BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF40174BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

5. Functional diagram

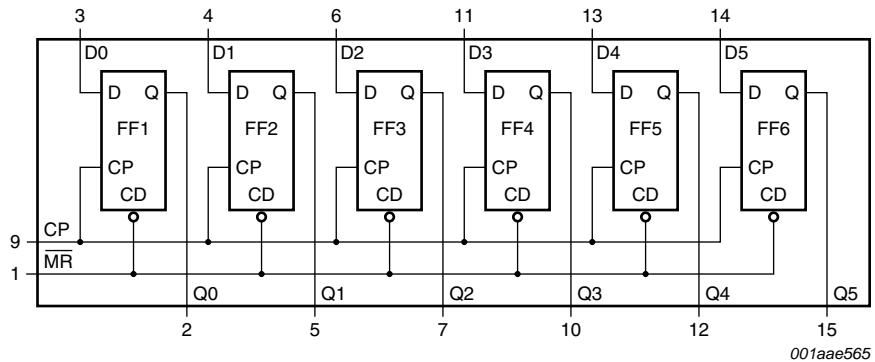


Fig 1. Functional diagram

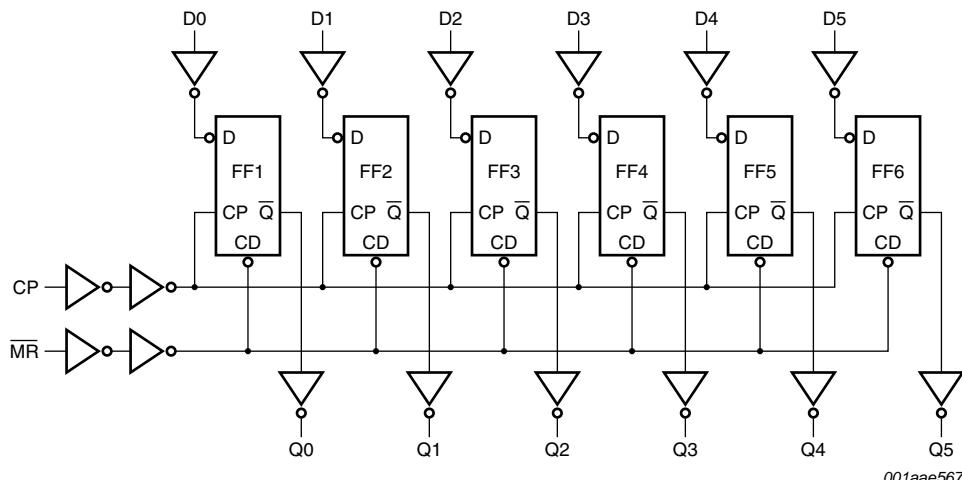


Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

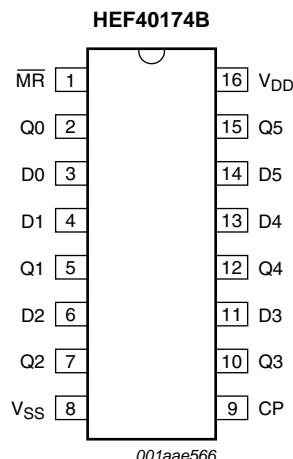


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
MR	1	master reset input (active LOW)
Q0, Q1, Q2, Q3, Q4, Q5	2, 5, 7, 10, 12, 15	buffered output
D0, D1, D2, D3, D4, D5	3, 4, 6, 11, 13, 14	data input
V _{SS}	8	ground supply voltage
CP	9	clock input (LOW-to-HIGH; edge-triggered)
V _{DD}	16	supply voltage

7. Functional description

Table 3. Function table^[1]

Input	Output		
CP	D	MR	Q
↑	H	H	H
↑	L	H	L
↓	X	H	no change
X	X	L	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
I_{IO}	input/output current		-	± 10	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-65	+150	$^{\circ}\text{C}$
T_{amb}	ambient temperature		-40	+85	$^{\circ}\text{C}$
P_{tot}	total power dissipation	DIP16 package	[1] -	750	mW
		SO16 package	[2] -	500	mW
P	power dissipation	per output	-	100	mW

[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 $^{\circ}\text{C}$.

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 $^{\circ}\text{C}$.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+85	$^{\circ}\text{C}$
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 \text{ V}$	-	-	3.75	$\mu\text{s}/\text{V}$
		$V_{DD} = 10 \text{ V}$	-	-	0.5	$\mu\text{s}/\text{V}$
		$V_{DD} = 15 \text{ V}$	-	-	0.08	$\mu\text{s}/\text{V}$

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0 \text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40 \text{ }^{\circ}\text{C}$		$T_{amb} = 25 \text{ }^{\circ}\text{C}$		$T_{amb} = 85 \text{ }^{\circ}\text{C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_O < 1 \mu\text{A}$	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$ I_O < 1 \mu\text{A}$	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V

Table 6. Static characteristics ...continued $V_{SS} = 0 \text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40^\circ\text{C}$		$T_{amb} = 25^\circ\text{C}$		$T_{amb} = 85^\circ\text{C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage $ I_O < 1 \mu\text{A}$		5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage $ I_O < 1 \mu\text{A}$		5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current $V_O = 2.5 \text{ V}$		5 V	-1.7	-	-1.4	-	-1.1	-	mA
			5 V	-0.52	-	-0.44	-	-0.36	-	mA
			10 V	-1.3	-	-1.1	-	-0.9	-	mA
			15 V	-3.6	-	-3.0	-	-2.4	-	mA
I_{OL}	LOW-level output current $V_O = 0.4 \text{ V}$		5 V	0.52	-	0.44	-	0.36	-	mA
			10 V	1.3	-	1.1	-	0.9	-	mA
			15 V	3.6	-	3.0	-	2.4	-	mA
I_I	input leakage current		15 V	-	± 0.3	-	± 0.3	-	± 1.0	μA
I_{DD}	supply current $I_O = 0 \text{ A}$		5 V	-	20	-	20	-	150	μA
			10 V	-	40	-	40	-	300	μA
			15 V	-	80	-	80	-	600	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics $V_{SS} = 0 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; or test circuit see [Figure 5](#); unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula		Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay CP to Qn; see Figure 4		5 V	$48 \text{ ns} + (0.55 \text{ ns/pF})C_L$		-	75	155	ns
			10 V	$19 \text{ ns} + (0.23 \text{ ns/pF})C_L$		-	30	65	ns
			15 V	$12 \text{ ns} + (0.16 \text{ ns/pF})C_L$		-	20	45	ns
	$\overline{\text{MR}}$ to Qn; see Figure 4		5 V	$58 \text{ ns} + (0.55 \text{ ns/pF})C_L$		-	85	175	ns
			10 V	$24 \text{ ns} + (0.23 \text{ ns/pF})C_L$		-	35	70	ns
			15 V	$17 \text{ ns} + (0.16 \text{ ns/pF})C_L$		-	25	50	ns
t_{PLH}	LOW to HIGH propagation delay CP to Qn; see Figure 4		5 V	$48 \text{ ns} + (0.55 \text{ ns/pF})C_L$		-	75	155	ns
			10 V	$19 \text{ ns} + (0.23 \text{ ns/pF})C_L$		-	30	65	ns
			15 V	$12 \text{ ns} + (0.16 \text{ ns/pF})C_L$		-	20	45	ns
t_t	transition time see Figure 4		5 V	$10 \text{ ns} + (1.00 \text{ ns/pF})C_L$		-	60	120	ns
			10 V	$9 \text{ ns} + (0.42 \text{ ns/pF})C_L$		-	30	60	ns
			15 V	$6 \text{ ns} + (0.28 \text{ ns/pF})C_L$		-	20	40	ns
t_{su}	set-up time Dn to CP; see Figure 4		5 V			20	10	-	ns
			10 V			10	5	-	ns
			15 V			10	5	-	ns

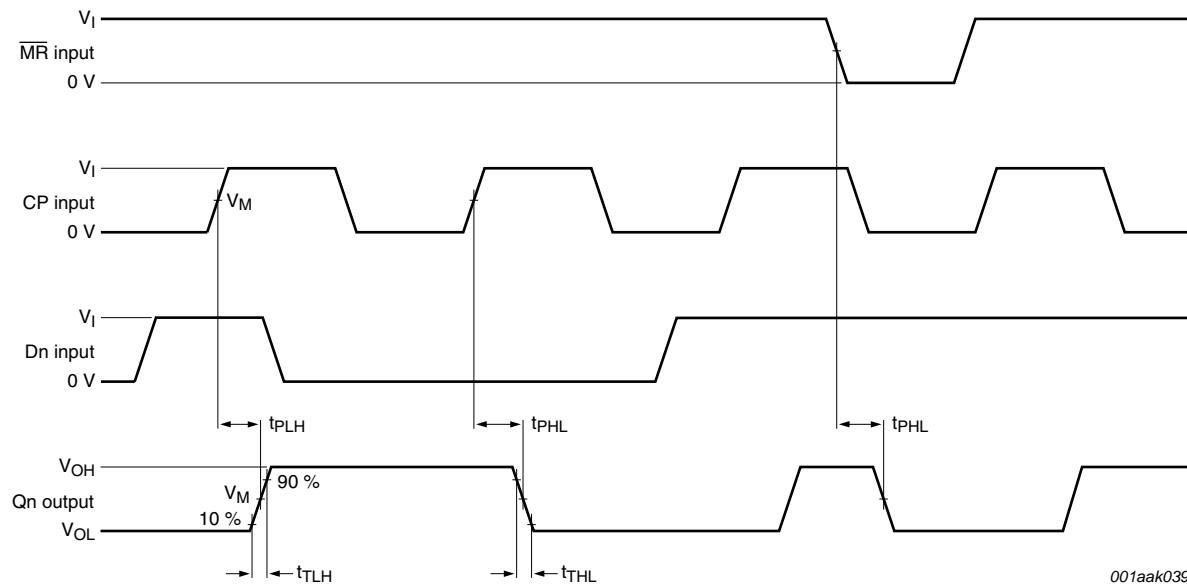
Table 7. Dynamic characteristics ...continued $V_{SS} = 0 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; or test circuit see [Figure 5](#); unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Typ	Max	Unit
t_h	hold time	Dn to CP; see Figure 4	5 V		10	0	-	ns
			10 V		5	0	-	ns
			15 V		5	0	-	ns
t_w	pulse width	CP input LOW; minimum width; see Figure 4	5 V		70	35	-	ns
			10 V		30	15	-	ns
			15 V		20	10	-	ns
		MR input LOW; minimum width; see Figure 4	5 V		70	35	-	ns
			10 V		35	15	-	ns
			15 V		25	10	-	ns
t_{rec}	recovery time	MR input; see Figure 4	5 V		45	25	-	ns
			10 V		20	10	-	ns
			15 V		15	5	-	ns
f_{max}	maximum frequency	see Figure 4	5 V		5	11	-	MHz
			10 V		15	30	-	MHz
			15 V		20	45	-	MHz

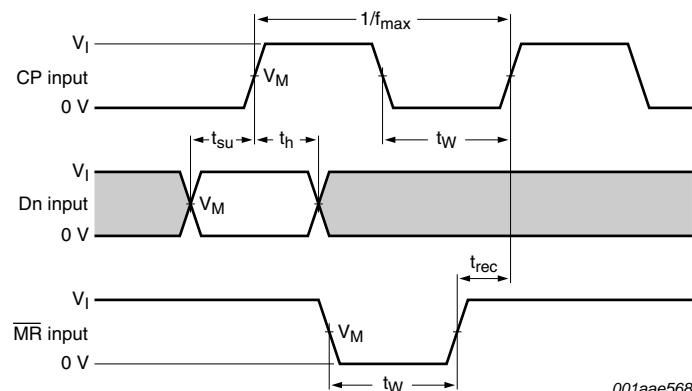
[1] t_t is the same as t_{THL} and t_{TLH} .**Table 8. Dynamic power dissipation P_D** P_D can be calculated from the formulas shown. $V_{SS} = 0 \text{ V}$; $t_i = t_f \leq 20 \text{ ns}$; $T_{amb} = 25^\circ\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 3500 \times f_i + \sum(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz, f_o = output frequency in MHz, C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\sum(f_o \times C_L)$ = sum of the outputs.
		10 V	$P_D = 16000 \times f_i + \sum(f_o \times C_L) \times V_{DD}^2$	
		15 V	$P_D = 42000 \times f_i + \sum(f_o \times C_L) \times V_{DD}^2$	

12. Waveforms



a. CP and \overline{MR} to Q_n Propagation delays and Q_n transition times



b. CP and \overline{MR} minimum pulse widths, \overline{MR} to CP recovery time, and Dn to CP set-up and hold times

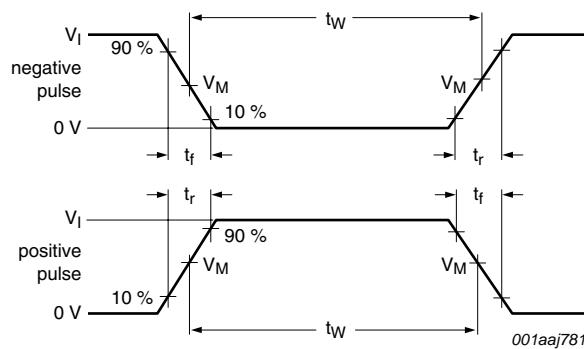
V_{OH} and V_{OL} are typical output voltage levels that occur with the output load.

Set-up and hold times are shown as positive values but may be specified as negative values.

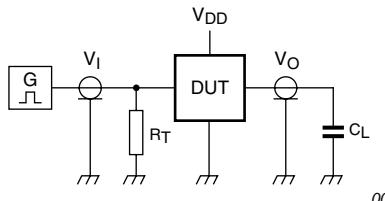
The shaded area are where input changes result in predictable output performance.

Measurement points are given in [Table 9](#).

Fig 4. Waveforms showing switching times



a. Input waveforms



b. Test circuit

Test data is given in [Table 9](#).

Definitions for test circuit:

DUT = Device Under Test

C_L = Load capacitance including jig and probe capacitance;

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 5. Test circuit for measuring switching times

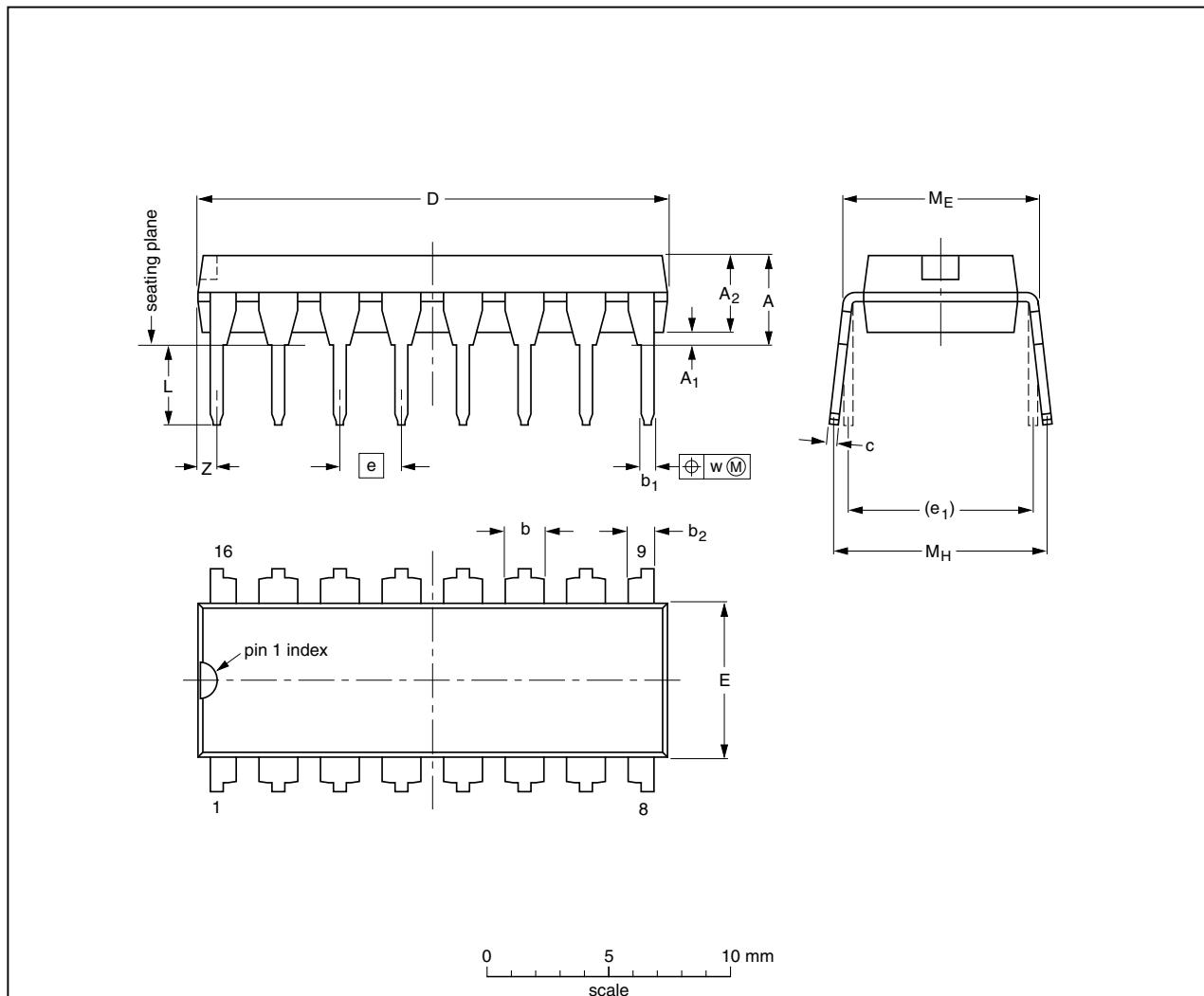
Table 9. Measurement points and test data

Supply voltage	Input			Load
	V_I	V_M	t_r, t_f	
5 V to 15 V	V_{DD}	$0.5V_I$	$\leq 20\text{ ns}$	50 pF

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

- Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						95-01-14 03-02-13

Fig 6. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

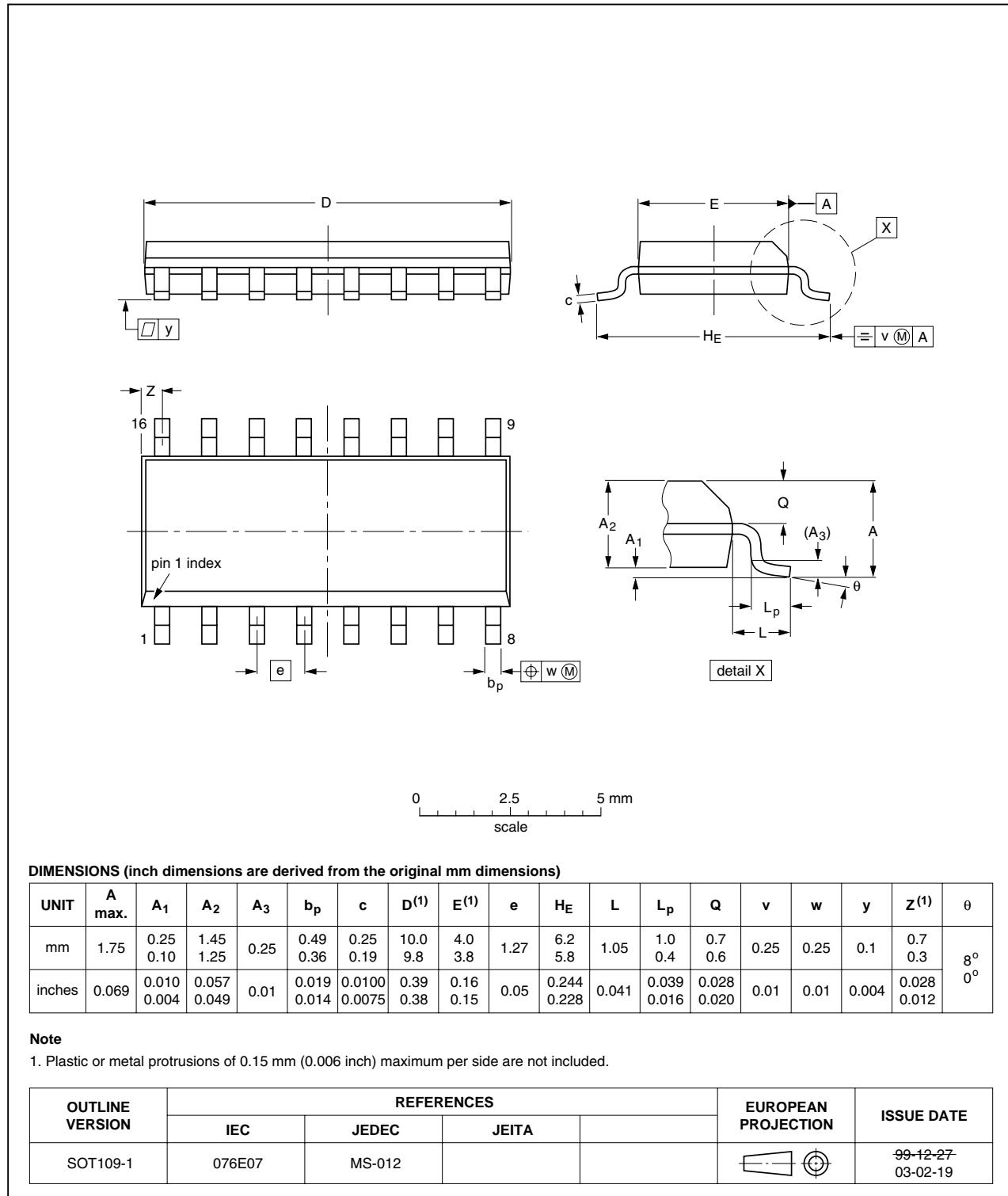


Fig 7. Package outline SOT109-1 (SO16)

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF40174B_5	20100106	Product data sheet	-	HEF40174B_4
Modifications:	• Section 9 “Recommended operating conditions” Δt/ΔV values updated.			
HEF40174B_4	20090813	Product data sheet	-	HEF40174B_CNV_3
HEF40174B_CNV_3	19950101	Product specification	-	HEF40174B_CNV_2
HEF40174B_CNV_2	19950101	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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